## **NPN Silicon Epitaxial Planar Transistor**

for switching and AF amplifier applications.

These transistors are subdivided into three groups Q, R and S according to their DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

## Absolute Maximum Ratings $(T_a = 25^{\circ}C)$

	Symbol	Value		Unit
		ST 2SC828	ST 2SC828A	
Collector Base Voltage	$V_{CBO}$	30	45	V
Collector Emitter Voltage	$V_{CEO}$	25	45	V
Emitter Base Voltage	$V_{EBO}$	7		V
Peak Collector Current	I <sub>CM</sub>	100		mA
Collector Current	I <sub>C</sub>	50		mA
Power Dissipation	P <sub>tot</sub>	400		mW
Junction Temperature	T <sub>j</sub>	150		°C
Storage Temperature Range	Ts	-55 to +150		°С









## ST 2SC828 / 828A

## Characteristics at T<sub>amb</sub>=25 °C

			Symbol	Min.	Тур.	Max.	Unit
DC Current Gain							
at I <sub>C</sub> =2mA, V <sub>CE</sub> =5V							
	Current Gain Group	Q	$h_{FE}$	130	-	280	-
		R	$h_{FE}$	180	-	360	-
		S	$h_{FE}$	260	-	520	-
Collector Base Breakdown Voltage							
at I <sub>C</sub> =10μA	ST 2SC828	3	$V_{(BR)CBO}$	30	-	-	V
	ST 2SC828	ЗА	$V_{(BR)CBO}$	45	-	-	V
Collector Emitter Breakdown Voltage							
at I <sub>C</sub> =2mA	ST 2SC828	3	$V_{(BR)CEO}$	25	-	-	V
	ST 2SC828	ВА	$V_{(BR)CEO}$	45	-	-	V
Emitter Base Breakdov	wn Voltage						
at $I_E=10\mu A$			$V_{(BR)EBO}$	7	-	-	V
Collector Saturation Vo	oltage						
at $I_C$ =50mA, $I_B$ =5mA			$V_{\text{CE(sat)}}$	-	0.14	-	V
Base Emitter Voltage							
at $I_C$ =10mA, $V_{CE}$ =5V			$V_{BE}$	-	-	0.8	V
Gain Bandwidth Produ	ct						
at $I_C$ =-2mA, $V_{CE}$ =10V			$f_{T}$	-	220	-	MHz
Noise Figure							
at $V_{CE}=5V,I_{E}=0.2mA$ ,			NF	-	6	-	dB
$R_G=2k\Omega$ ,f=1kHz							







